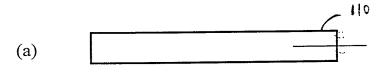


(PRIOR ART)

- F16.1A



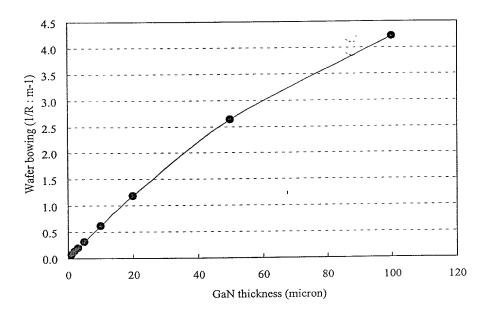


GaN layer or InGaN/AlGaN device layers

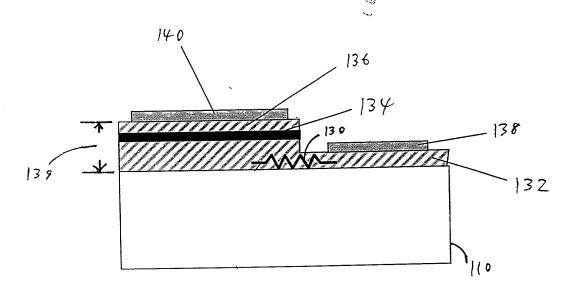


" (PRIOR ART)

F16.1B

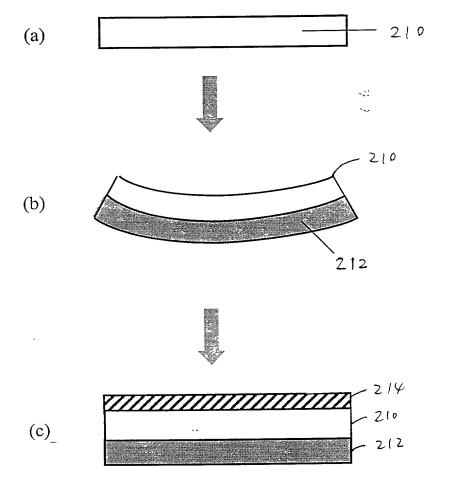


(PRIOR ART)

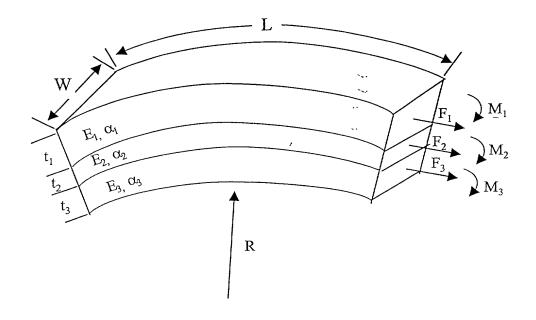


(PRIOR ART)

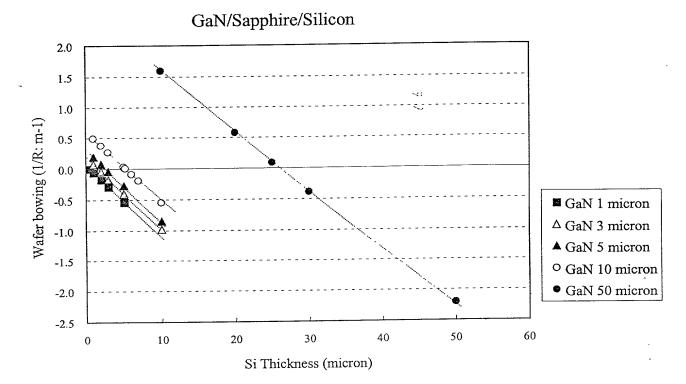
FIG. (D



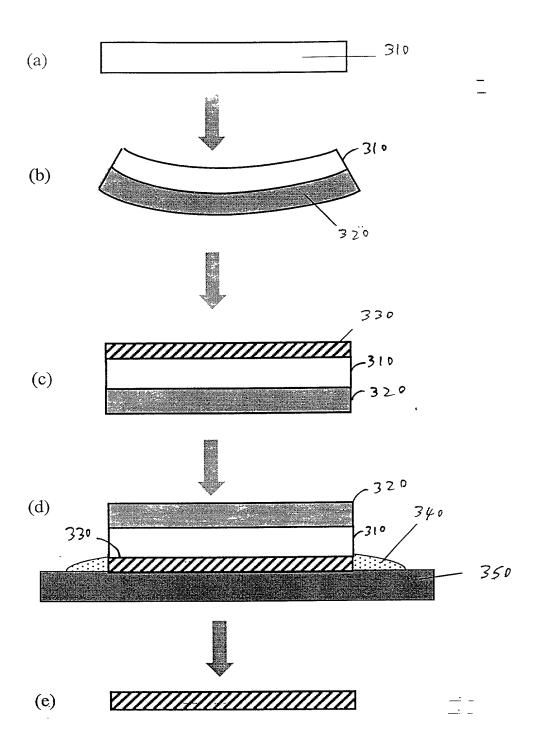
- 616.2A



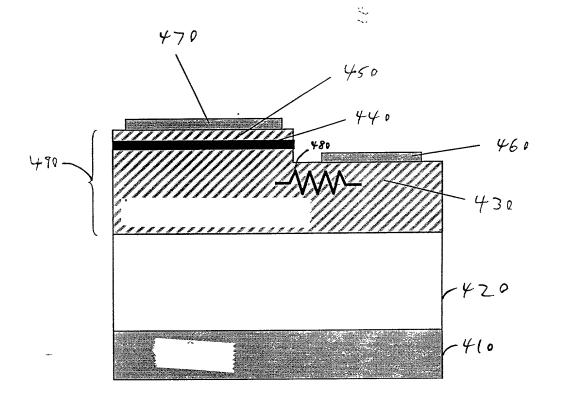
F16.2B



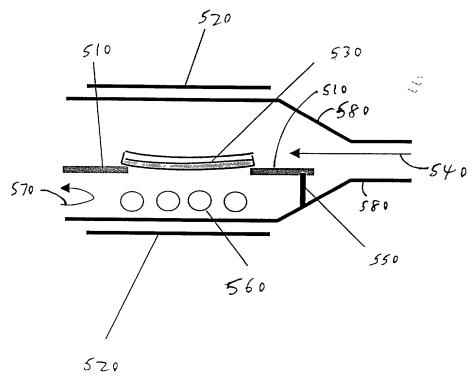
F16,20



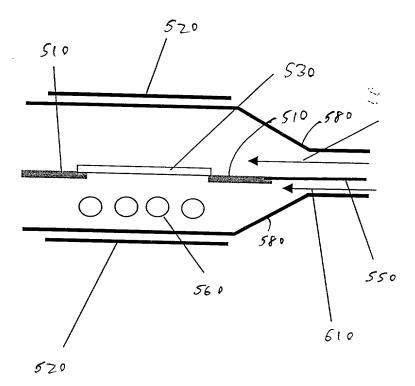
F16.3



E16.4



F16.5



F16-6

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